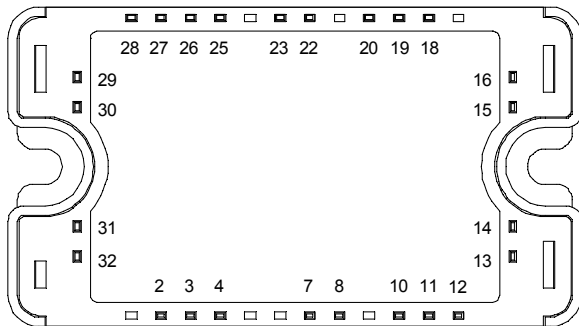
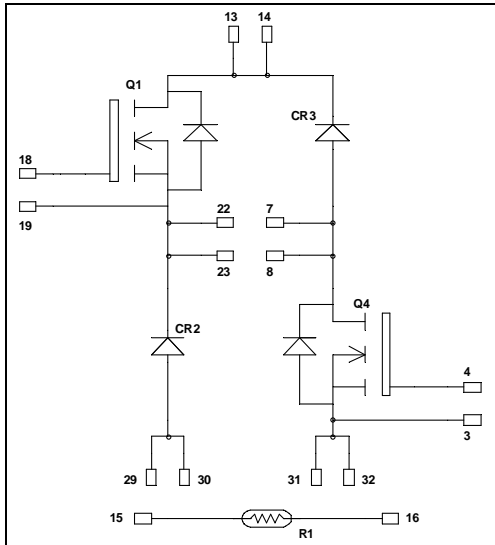


Asymmetrical Bridge Super Junction MOSFET Power Module

$V_{DSS} = 600V$
 $R_{DSon} = 24m\Omega \text{ max @ } T_j = 25^\circ C$
 $I_D = 95A \text{ @ } T_c = 25^\circ C$



All multiple inputs and outputs must be shorted together
 Example: 13/14 ; 29/30 ; 22/23...

Application

- Welding converters
- Switched Mode Power Supplies
- Switched Reluctance Motor Drives

Features

- **COOLMOS**
Power Semiconductors
 - Ultra low R_{DSon}
 - Low Miller capacitance
 - Ultra low gate charge
 - Avalanche energy rated
 - Very rugged
- Kelvin source for easy drive
- Very low stray inductance
 - Symmetrical design
- Internal thermistor for temperature monitoring
- High level of integration

Benefits

- Outstanding performance at high frequency operation
- Direct mounting to heatsink (isolated package)
- Low junction to case thermal resistance
- Solderable terminals both for power and signal for easy PCB mounting
- Low profile
- RoHS compliant

Absolute maximum ratings

Symbol	Parameter	Max ratings	Unit
V_{DSS}	Drain - Source Breakdown Voltage	600	V
I_D	Continuous Drain Current	$T_c = 25^\circ C$	95
		$T_c = 80^\circ C$	70
I_{DM}	Pulsed Drain current	260	A
V_{GS}	Gate - Source Voltage	± 20	V
R_{DSon}	Drain - Source ON Resistance	24	$m\Omega$
P_D	Maximum Power Dissipation	$T_c = 25^\circ C$	462
I_{AR}	Avalanche current (repetitive and non repetitive)	15	A
E_{AR}	Repetitive Avalanche Energy	3	mJ
E_{AS}	Single Pulse Avalanche Energy	1900	

CAUTION: These Devices are sensitive to Electrostatic Discharge. Proper Handling Procedures Should Be Followed. See application note APT0502 on www.microsemi.com

All ratings @ $T_j = 25^\circ\text{C}$ unless otherwise specified

Electrical Characteristics

Symbol	Characteristic	Test Conditions	Min	Typ	Max	Unit
I_{DSS}	Zero Gate Voltage Drain Current	$V_{GS} = 0V, V_{DS} = 600V$ $T_j = 25^\circ\text{C}$			350	μA
		$V_{GS} = 0V, V_{DS} = 600V$ $T_j = 125^\circ\text{C}$			600	
$R_{DS(on)}$	Drain – Source on Resistance	$V_{GS} = 10V, I_D = 47.5A$			24	$\text{m}\Omega$
$V_{GS(th)}$	Gate Threshold Voltage	$V_{GS} = V_{DS}, I_D = 5\text{mA}$	2.1	3	3.9	V
I_{GSS}	Gate – Source Leakage Current	$V_{GS} = \pm 20V, V_{DS} = 0V$			200	nA

Dynamic Characteristics

Symbol	Characteristic	Test Conditions	Min	Typ	Max	Unit
C_{iss}	Input Capacitance	$V_{GS} = 0V ; V_{DS} = 25V$ $f = 1\text{MHz}$		14.4		nF
C_{oss}	Output Capacitance			17		
Q_g	Total gate Charge	$V_{GS} = 10V$ $V_{Bus} = 300V$ $I_D = 95A$		300		nC
Q_{gs}	Gate – Source Charge			68		
Q_{gd}	Gate – Drain Charge			102		
$T_{d(on)}$	Turn-on Delay Time	Inductive Switching (125°C) $V_{GS} = 10V$ $V_{Bus} = 400V$ $I_D = 95A$ $R_G = 2.5\Omega$		21		ns
T_r	Rise Time			30		
$T_{d(off)}$	Turn-off Delay Time			100		
T_f	Fall Time			45		
E_{on}	Turn-on Switching Energy	Inductive switching @ 25°C $V_{GS} = 10V ; V_{Bus} = 400V$ $I_D = 95A ; R_G = 2.5\Omega$		1350		μJ
E_{off}	Turn-off Switching Energy			1040		
E_{on}	Turn-on Switching Energy	Inductive switching @ 125°C $V_{GS} = 10V ; V_{Bus} = 400V$ $I_D = 95A ; R_G = 2.5\Omega$		2200		μJ
E_{off}	Turn-off Switching Energy			1270		

Diode ratings and characteristics

Symbol	Characteristic	Test Conditions	Min	Typ	Max	Unit
V_{RRM}	Maximum Peak Repetitive Reverse Voltage		600			V
I_{RM}	Maximum Reverse Leakage Current	$V_R = 600V$	$T_j = 25^\circ\text{C}$		25	μA
			$T_j = 125^\circ\text{C}$		500	
I_F	DC Forward Current	$T_c = 80^\circ\text{C}$		60		A
V_F	Diode Forward Voltage	$I_F = 60A$		1.7	2.3	V
		$I_F = 120A$		2		
		$I_F = 60A$ $T_j = 125^\circ\text{C}$		1.4		
t_{rr}	Reverse Recovery Time	$I_F = 60A$ $V_R = 400V$ $di/dt = 200A/\mu\text{s}$	$T_j = 25^\circ\text{C}$	70		ns
			$T_j = 125^\circ\text{C}$	140		
Q_{rr}	Reverse Recovery Charge	$I_F = 60A$ $V_R = 400V$ $di/dt = 200A/\mu\text{s}$	$T_j = 25^\circ\text{C}$	100		nC
			$T_j = 125^\circ\text{C}$	690		

Thermal and package characteristics

Symbol	Characteristic	Min	Typ	Max	Unit	
R _{thJC}	Junction to Case Thermal Resistance	CoolMOS		0.27	°C/W	
		diode		0.85		
V _{ISOL}	RMS Isolation Voltage, any terminal to case t=1 min, I _{isol} <1mA, 50/60Hz	4000			V	
T _J	Operating junction temperature range	-40		150	°C	
T _{STG}	Storage Temperature Range	-40		125		
T _C	Operating Case Temperature	-40		100		
Torque	Mounting torque	To heatsink	M4	2.5	4.7	N.m
Wt	Package Weight				110	g

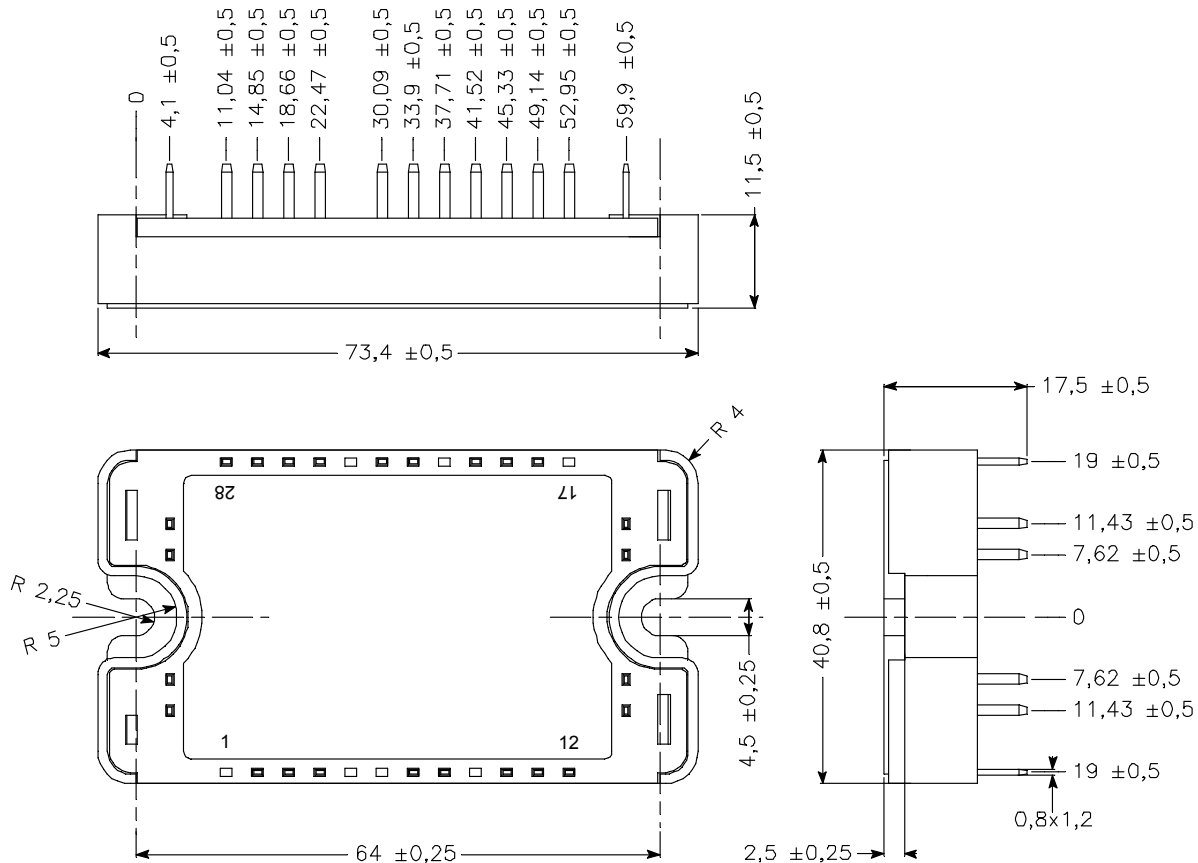
Temperature sensor NTC (see application note APT0406 on www.microsemi.com for more information).

Symbol	Characteristic	Min	Typ	Max	Unit
R ₂₅	Resistance @ 25°C		50		kΩ
ΔR ₂₅ /R ₂₅			5		%
B _{25/85}	T ₂₅ = 298.15 K		3952		K
ΔB/B	T _C = 100°C		4		%

$$R_T = \frac{R_{25}}{\exp \left[B_{25/85} \left(\frac{1}{T_{25}} - \frac{1}{T} \right) \right]}$$

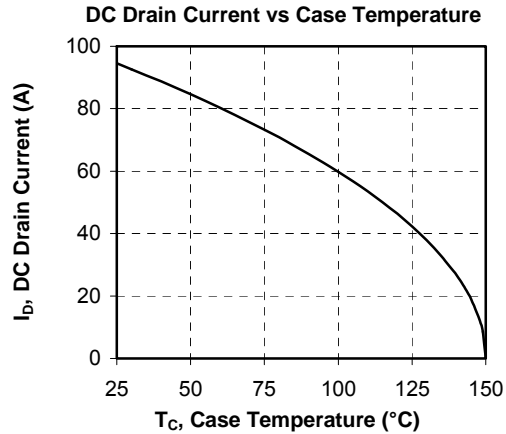
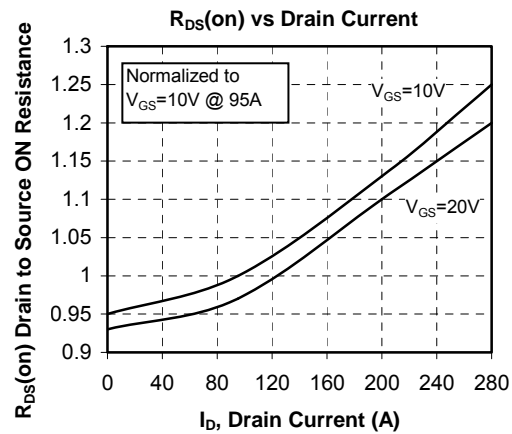
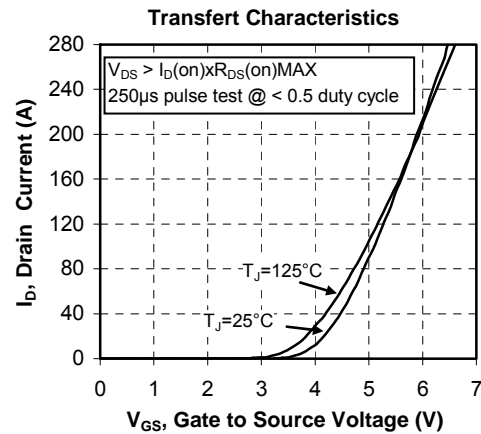
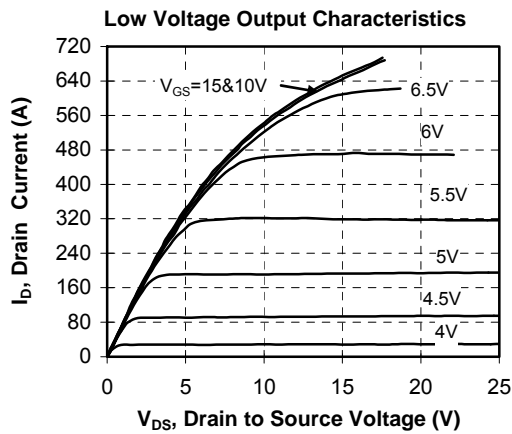
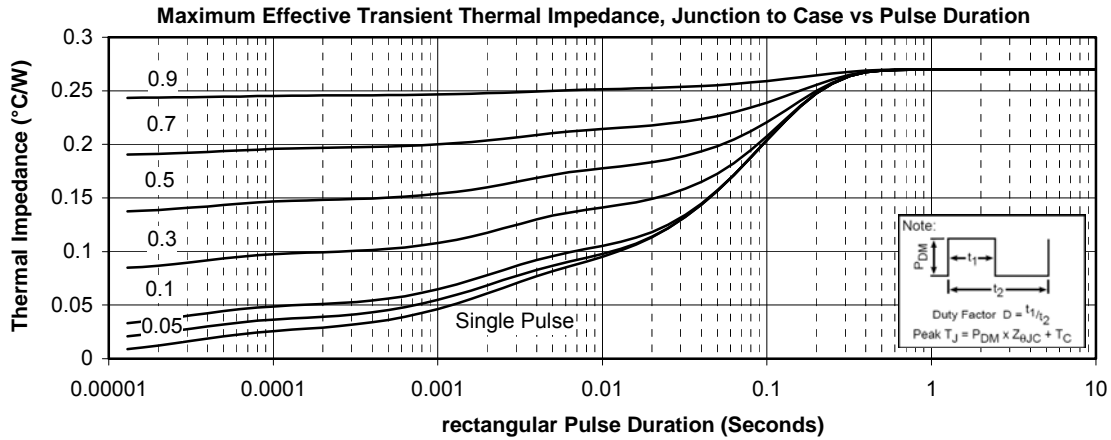
T: Thermistor temperature
 R_T: Thermistor value at T

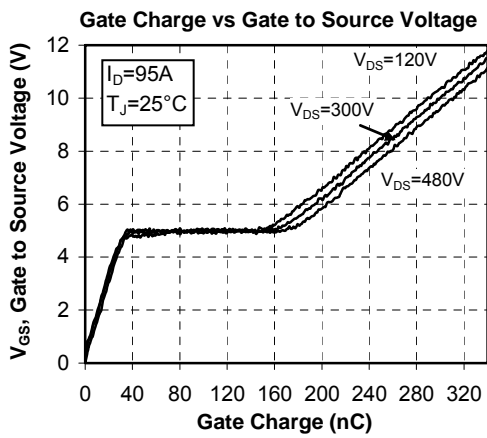
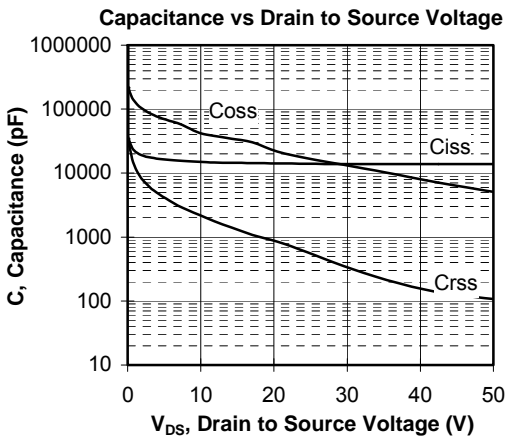
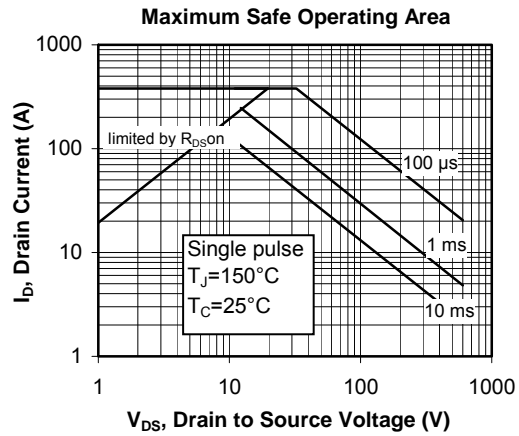
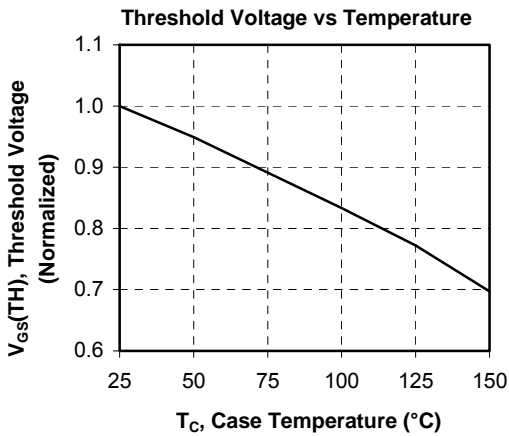
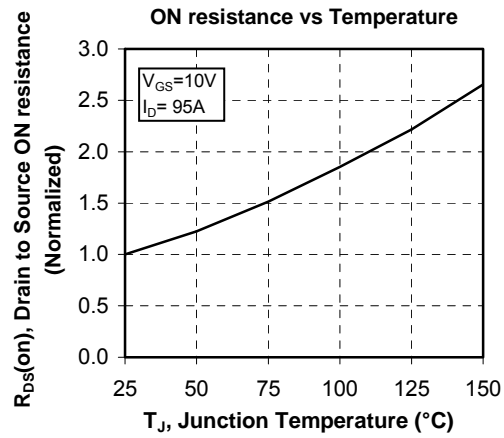
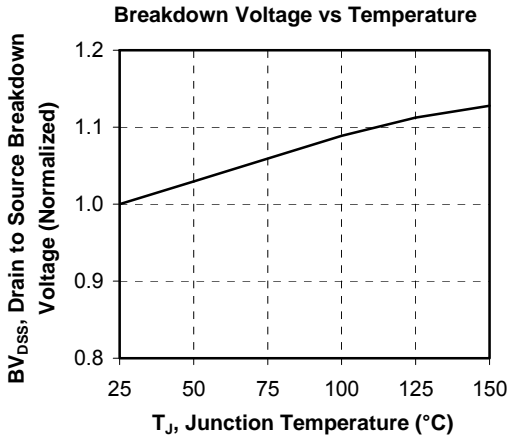
SP3 Package outline (dimensions in mm)

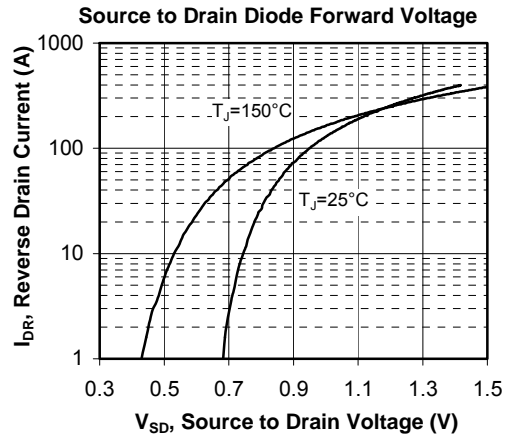
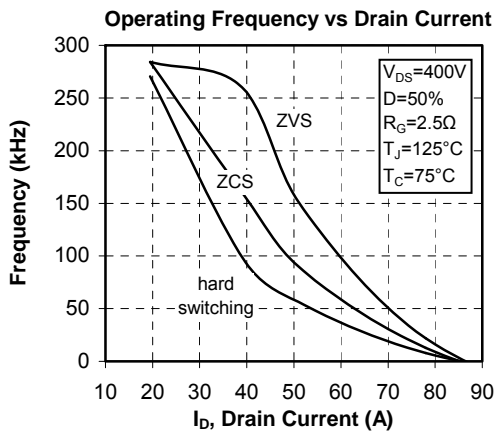
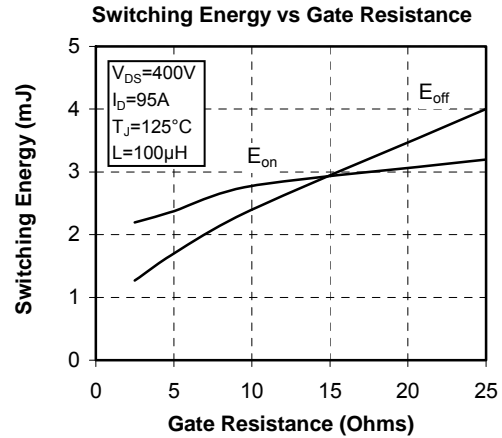
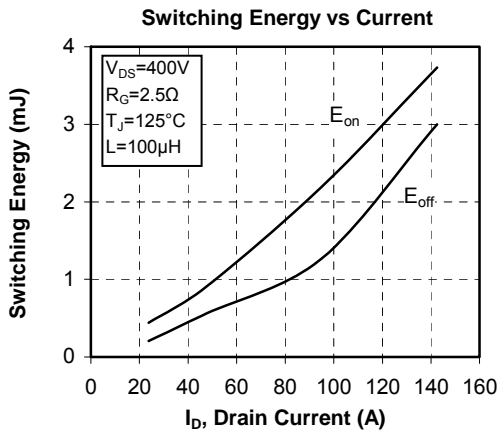
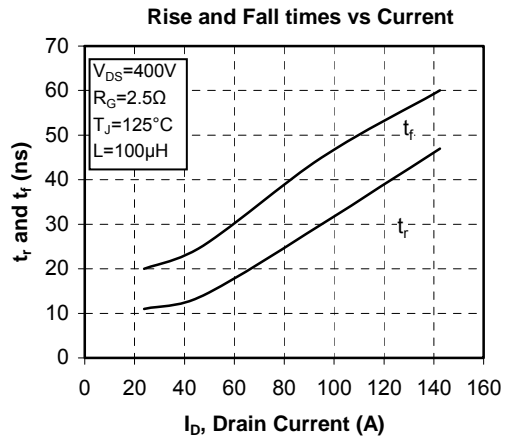
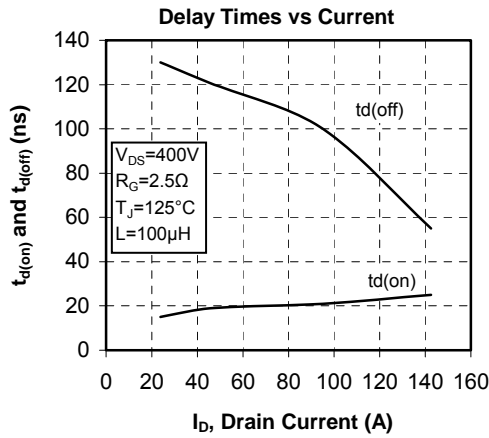


See application note 1901 - Mounting Instructions for SP3 Power Modules on www.microsemi.com

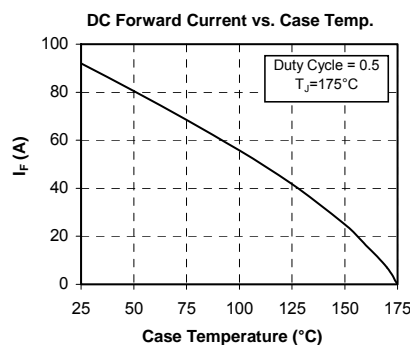
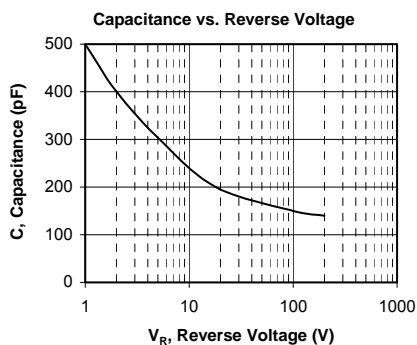
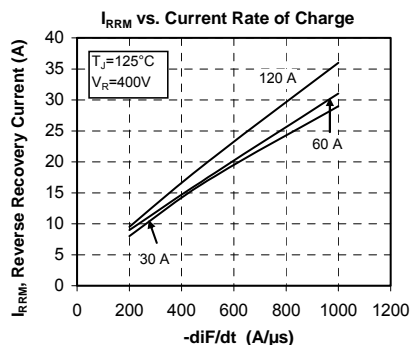
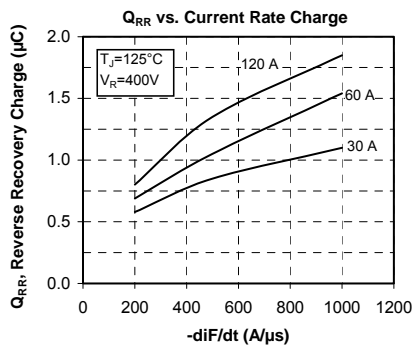
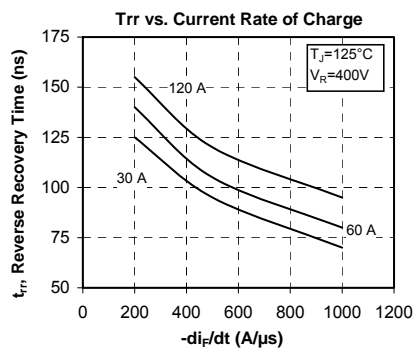
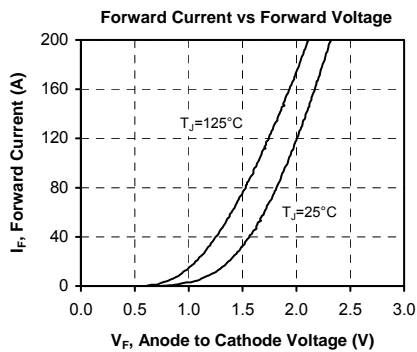
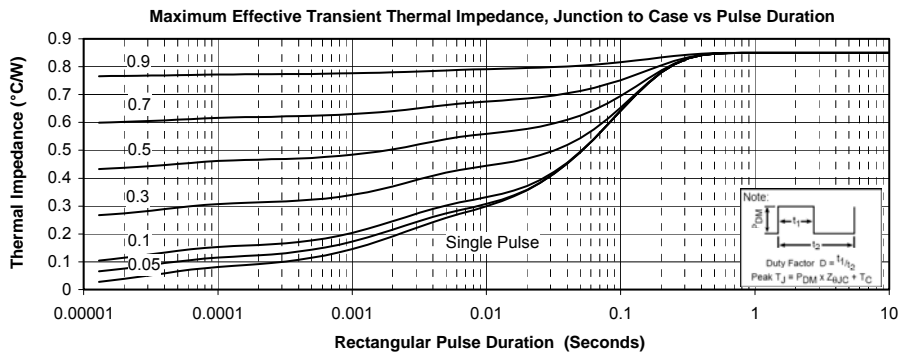
Typical CoolMOS Performance Curve







Typical diode Performance Curve



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Microsemi's products are covered by one or more of U.S patents 4,895,810 5,045,903 5,089,434 5,182,234 5,019,522 5,262,336 6,503,786 5,256,583 4,748,103 5,283,202 5,231,474 5,434,095 5,528,058 6,939,743 7,352,045 5,283,201 5,801,417 5,648,283 7,196,634 6,664,594 7,157,886 6,939,743 7,342,262 and foreign patents. U.S and Foreign patents pending. All Rights Reserved.